

NOT RECOMMENDED FOR NEW DESIGN -NO ALTERNATE PART



DMJ70H900HJ3

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _{D Max} T _C = +25°C	
700V	0.9Ω @ $V_{GS} = 10V$	7A	

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

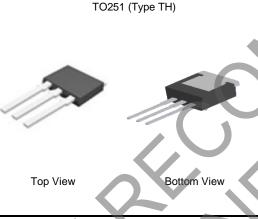
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

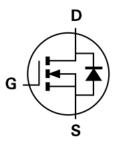
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Mechanical Data

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.33 grams (Approximate)







Top View Pin Configuration

Internal Schematic

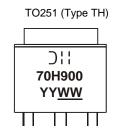
Ordering Information (Note 4)

Part Number	Case	Packaging
DMJ70H900HJ3	TO251 (Type TH)	75 Pieces / Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	700	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Ocaliana Paris Ocasa (Nata 5) V 40V	T _C = +25°C		7	- A
Continuous Drain Current (Note 5) V _{GS} = 10V	T _C = +100°C	ID	4	
Maximum Body Diode Forward Current (Note 6)	•	Is	1.6	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	10	А
Avalanche Current (Note 7)	L = 60mH	I _{AS}	1.3	А
Avalanche Energy (Note 7)	L = 60mH	E _{AS}	50	mJ
Peak Diode Recovery dv/dt (Note 7)		dv/dt	8	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

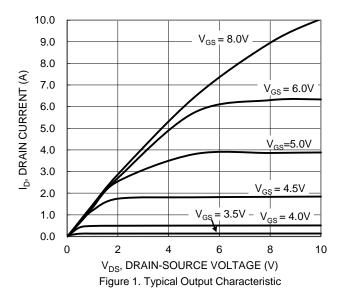
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$	PD	68	w
Thermal Resistance, Junction to Ambient (Note 6)		R _{θJA}	79	°C/W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	1.8	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	700		/ -	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	1	1	1	μΑ	V _{DS} = 700V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}		17	100	nA	$V_{GS} = \pm 30V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	3.4	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		0.7	0.9	Ω	$V_{GS} = 10V, I_D = 1.5A$	
Diode Forward Voltage	V _{SD}		0.85	1.3	V	$V_{GS} = 0V, I_{S} = 5A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		603	_		$V_{DS} = 50V$, $f = 1MHz$, $V_{GS} = 0V$	
Output Capacitance	Coss		230	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	16	_			
Gate Resistance	R_g	_	4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	18.4	_		V 500V I 54	
Gate-Source Charge	Q _{gs}	_	2.1	_	nC	$V_{DD} = 560V, I_D = 5A,$	
Gate-Drain Charge	Q_{gd}	_	9.8	_		$V_{GS} = 10V$	
Turn-On Delay Time	t _{D(ON)}		8.7	_		$V_{DD} = 350V, V_{GS} = 10V,$ $R_g = 4.7\Omega, I_D = 5A$	
Turn-On Rise Time	t _R	_	18.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	28.5	_	115		
Turn-Off Fall Time	t _F	_	10.7	_			
Body Diode Reverse Recovery Time	t _{RR}	_	239	_	ns	I _S = 5A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q_{RR}		2.2	_	μC	15 = 5A, αι/αι = 100A/μS	

Notes:

- 5. Device mounted on infinite heatsink.
- 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
- Guaranteed by design. Not subject to production testing.
 Short duration pulse test used to minimize self-heating effect.



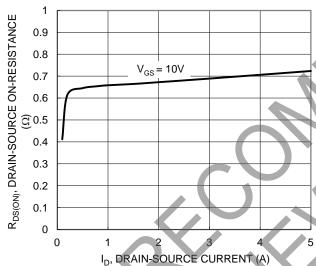


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

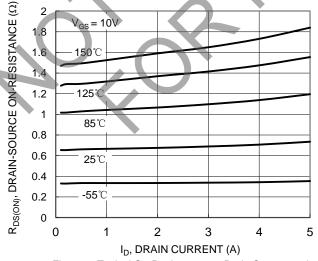


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

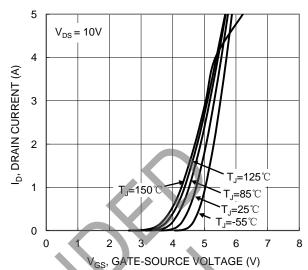


Figure 2. Typical Transfer Characteristic

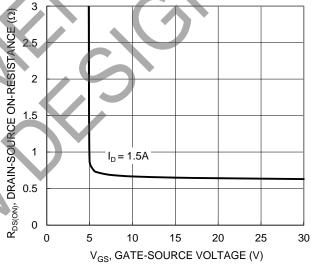


Figure 4. Typical Transfer Characteristic

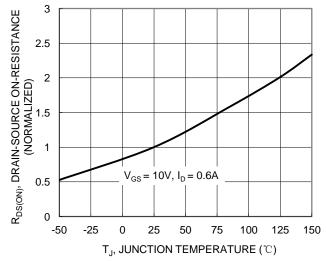


Figure 6. On-Resistance Variation with Temperature



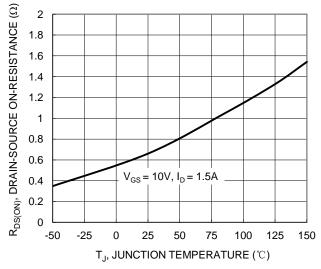
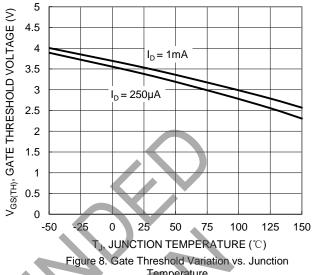
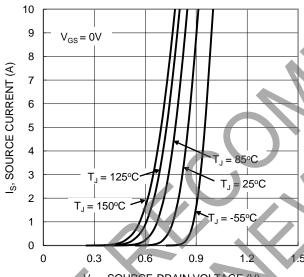


Figure 7. On-Resistance Variation with Temperature



Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

 $V_{DS} = 560V, I_{D} = 5A$

16 18

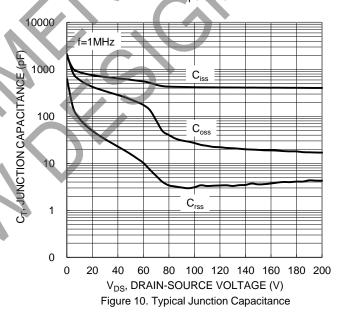
14

8 10 12

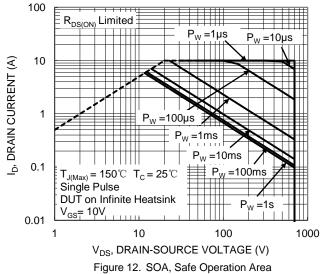
Qq (nC)

Figure 11. Gate Charge

6



20



0

2 4

V_{GS} (V) €

2

0



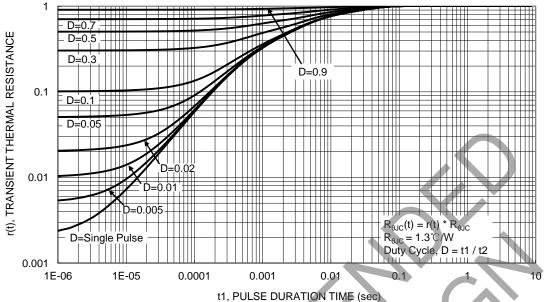


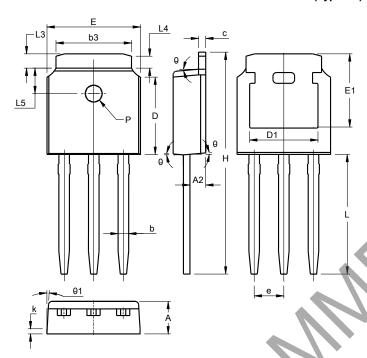
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO251 (Type TH)



TO251 (Type TH)						
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b3	5.20	5.50	5.33			
С	0.43	0.63	0.53			
D	5.98	6.22	6.10			
D1	4,	5.30 REF	=			
е	2	.286 BS	C			
E	6.40	6.80	6.60			
E1	4.63	5.03	4.83			
Ħ,	16.22	16.82	16.52			
k	0.40REF					
	9.15	9.65	9.40			
L3	0.88	1.28	1.02			
L4.	0.75 REF					
L5	1.65	1.95	1.80			
PØ	1.20					
θ	5°	9°	7°			
θ1	5°	9°	7°			
All Dimensions in mm						



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